

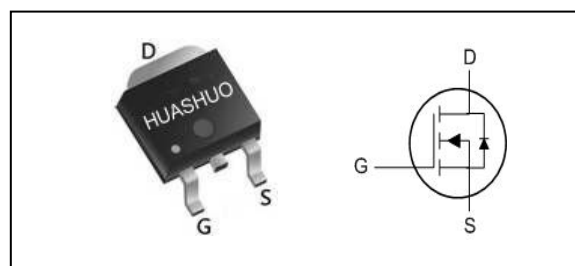
N-Ch 40V Fast Switching MOSFETs
Description

- Advanced Trench Technology
- Low Gate Charge
- 100% UIS Tested
- Low Gate Charge

- SMPS Synchronous Rectification
- DC/DC Converters
- Or-ing

Product Summary

V_{DS}	40	V
$R_{DS(ON),typ}$	4.7	m Ω
I_D	50	A

TO-252 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current ¹	50	A
$I_D@T_C=100^\circ C$	Continuous Drain Current ¹	31	A
I_{DM}	Pulsed Drain Current ²	90	A
EAS	Single Pulse Avalanche Energy ³	68	mJ
I_{AS}	Avalanche Current	37	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	70	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) ¹	---	55	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	1.7	$^\circ C/W$

Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	40	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=15A$	---	4.7	6.5	m Ω
		$V_{GS}=4.5V, I_D=15A$	---	7.5	10.5	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.9	2.2	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=32V, V_{GS}=0V, T_J=25^\circ C$	---	---	1	μA
		$V_{DS}=32V, V_{GS}=0V, T_J=55^\circ C$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	---	1.9	---	Ω
Q_g	Total Gate Charge	$V_{DS}=20V, V_{GS}=10V, I_D=15A$	---	20	---	nC
Q_{gs}	Gate-Source Charge		---	3.5	---	
Q_{gd}	Gate-Drain Charge		---	4.2	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=20V, V_{GS}=10V, R_G=3\Omega, I_D=15A$	---	12	---	ns
T_r	Rise Time		---	9.6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	21	---	
T_f	Fall Time		---	16	---	
C_{iss}	Input Capacitance	$V_{DS}=20V, V_{GS}=0V, f=1MHz$	---	950	---	μF
C_{oss}	Output Capacitance		---	493	---	
C_{rss}	Reverse Transfer Capacitance		---	48	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	50	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ C$	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=37A$
- 4.The power dissipation is limited by 150 $^\circ C$ junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

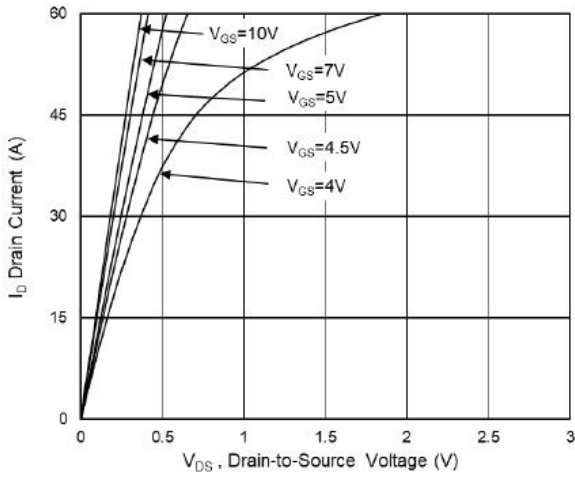


Fig.1 Typical Output Characteristics

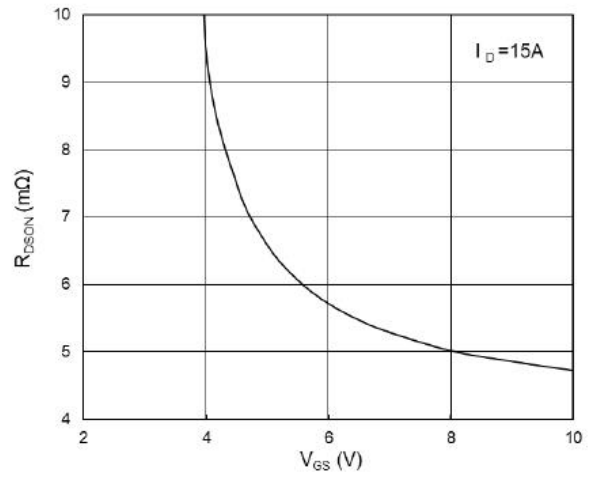


Fig.2 On-Resistance vs. G-S Voltage

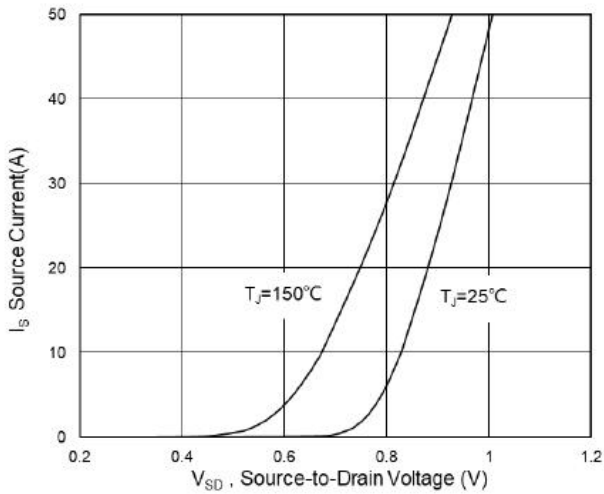


Fig.3 Source Drain Forward Characteristics

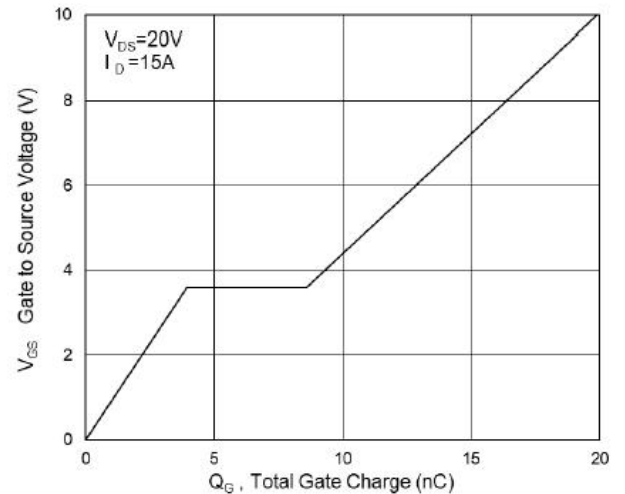


Fig.4 Gate-Charge Characteristics

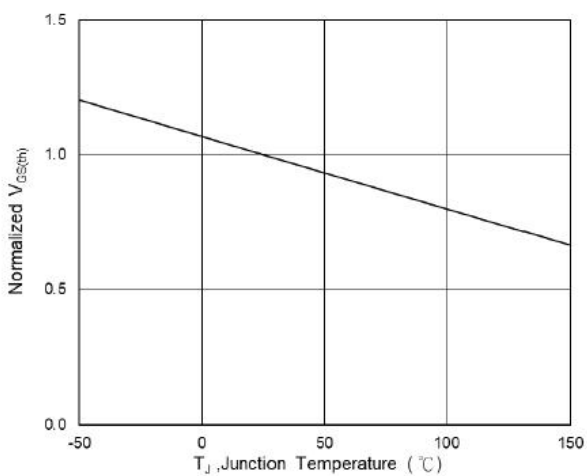


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

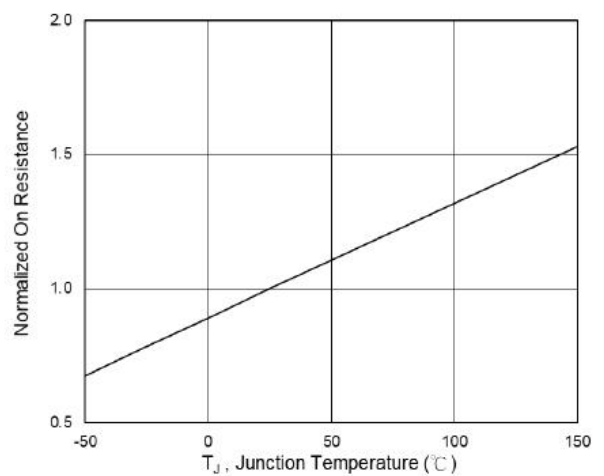


Fig.6 Normalized $R_{DS(on)}$ vs. T_J



N-Ch 40V Fast Switching MOSFETs

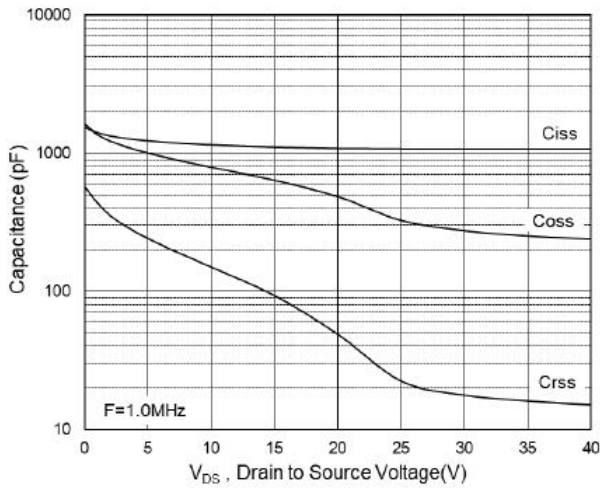


Fig.7 Capacitance

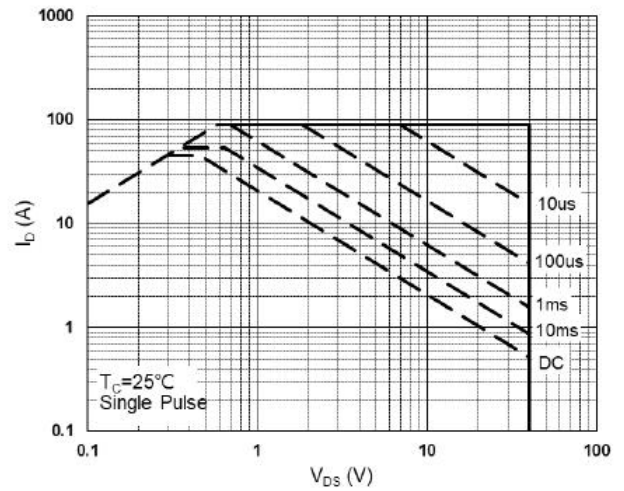


Fig.8 Safe Operating Area

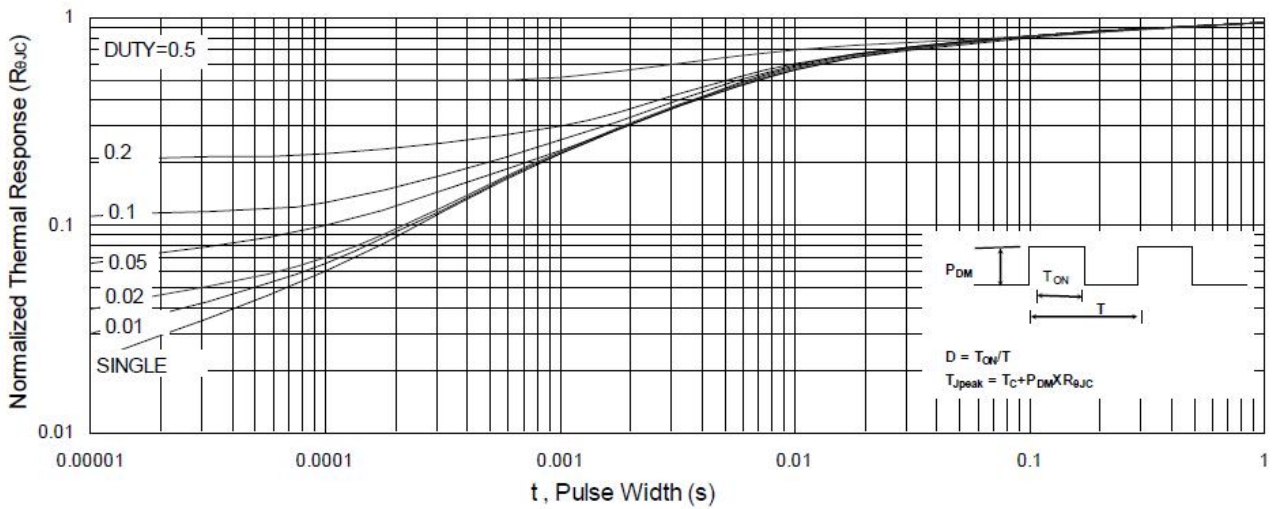


Fig.9 Normalized Maximum Transient Thermal Impedance

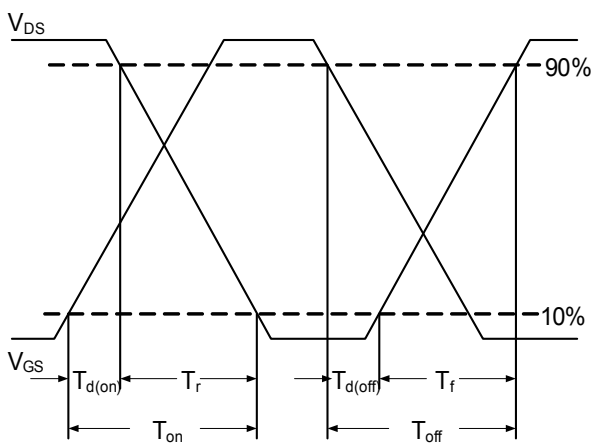


Fig.10 Switching Time Waveform

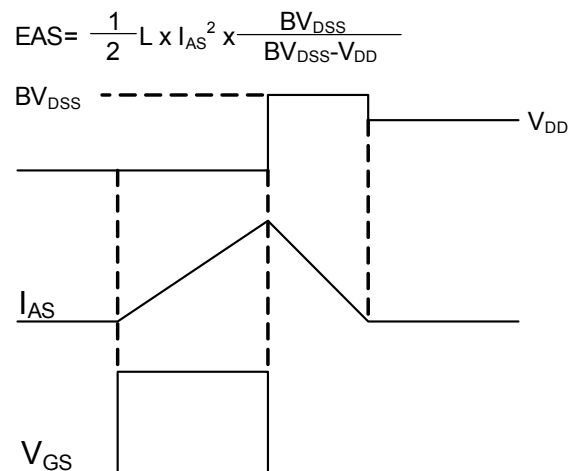
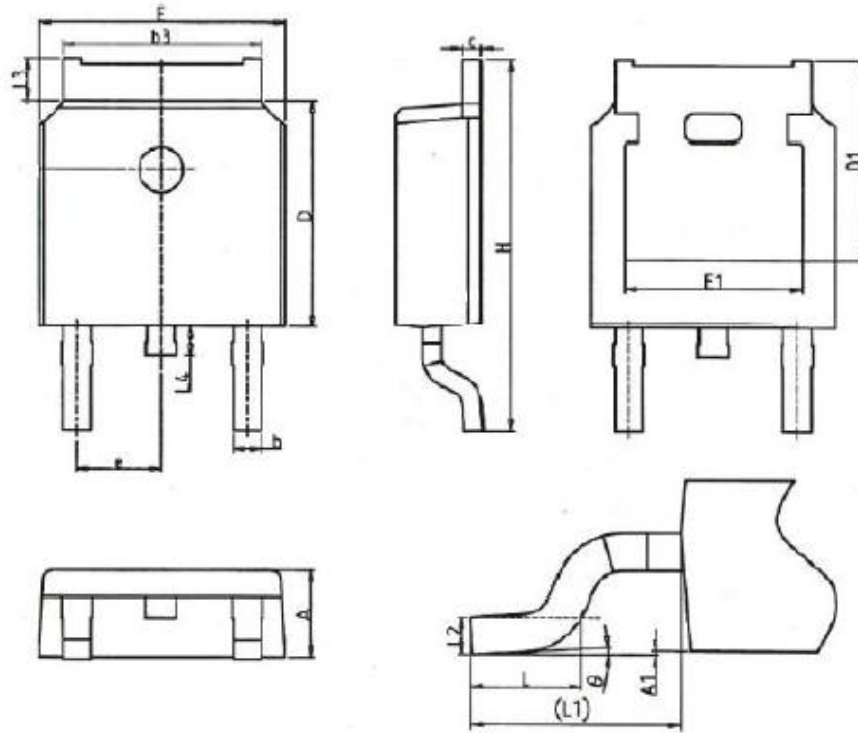


Fig.11 Unclamped Inductive Waveform

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



TO252-2L Package Outline



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.18	2.40	0.086	0.095
A1	-	0.2	-	0.008
b	0.68	0.9	0.026	0.036
b3	4.95	5.46	0.194	0.215
c	0.43	0.89	0.017	0.035
D	5.97	6.22	0.235	0.245
D1	5.300REF		0.209REF	
E	6.35	6.73	0.250	0.265
E1	4.32	--	0.170	-
e	2.286BSC		0.09BSC	
H	9.4	10.5	0.370	0.413
L	1.38	1.78	0.054	0.070
L1	2.90REF		0.114REF	
L2	0.51BSC		0.020BSC	
L3	0.88	1.28	0.034	0.050
L4	0.5	1	0.019	0.039
θ	0°	8°	0°	8°

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